

Silicon Epitaxial Planar Transistor

2SD1757K

FEATURES

- Low $V_{CE(sat)}$ (Typ. 8mV at $I_C/I_B=10/1mA$)
- Optimal for muting.
- Power dissipation. $P_D=200mW$.

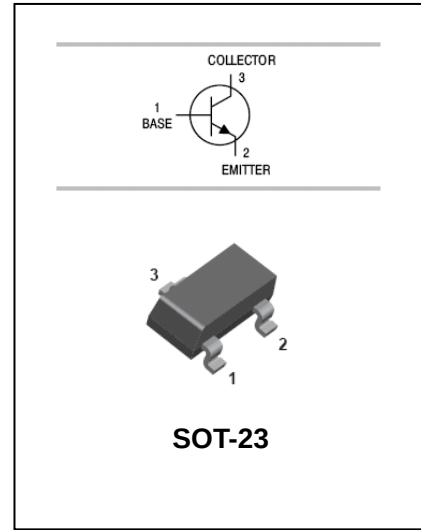


APPLICATIONS

- Audio frequency general.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SD1757K	AAQ/AAR/AAS	SOT-23



MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	6.5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}C$

Silicon Epitaxial Planar Transistor**2SD1757K****ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_C=50\mu A, I_C=0$	6.5			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=3V, I_C=100mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$		0.1	0.25	V
Transition frequency	f_T	$V_{CE}=5V, I_C=50mA$ $f=100MHz$		150		MHz
Output capacitance	C_{ob}	$V_{CB}=5V, I_E=0A, f=1MHz$		15		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	AAQ	AAR	AAS

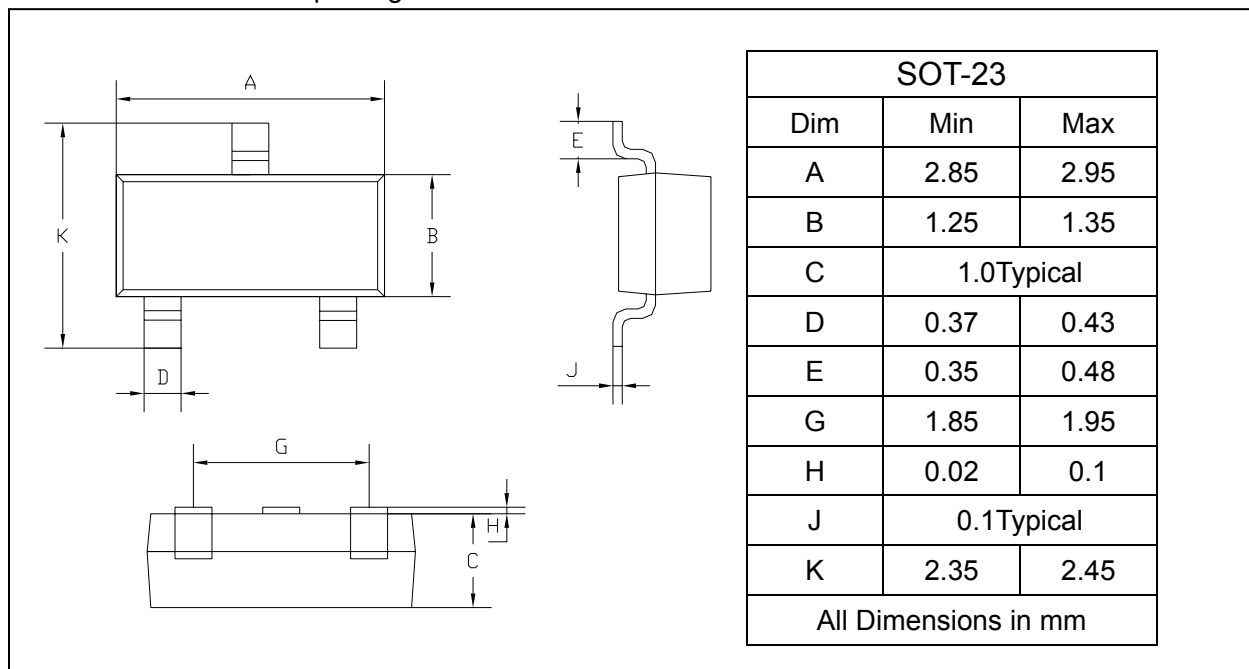
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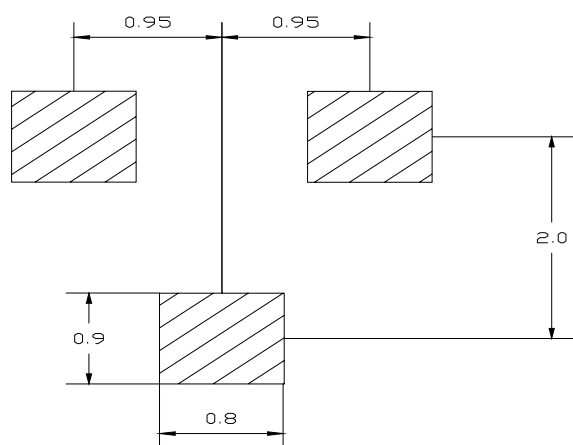
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SD1757K	SOT-23	3000/Tape&Reel